

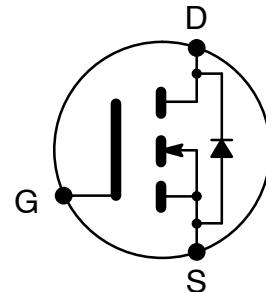


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**NTE2923  
MOSFET  
N-Ch, Enhancement Mode  
High Speed Switch  
TO247 Type Package**

**Features:**

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Parallelizing
- Simple Drive Requirements



**Absolute Maximum Ratings:**

|  |                          |
|--|--------------------------|
| Continuous Drain Current ( $V_{GS} = 10V$ ), $I_D$                                 |                          |
| $T_C = +25^\circ C$ .....  | 8.8A                     |
| $T_C = +100^\circ C$ .....   | 5.6A                     |
| Pulsed Drain Current (Note 1), $I_{DM}$ .....                                      | 35A                      |
| Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....                             | 150W                     |
| Derate Linearly Above $25^\circ C$ .....   | 1.2W/ $^\circ C$         |
| Gate-to-Source Voltage, $V_{GS}$ .....   | $\pm 20$                 |
| Single Pulse Avalanche Energy (Note 2), $E_{AS}$ .....                             | 480mJ                    |
| Avalanche Current (Note 1), $I_{AR}$ .....   | 8.8A                     |
| Repetitive Avalanche Energy (Note 1), $E_{AR}$ .....                               | 15mJ                     |
| Peak Diode Recovery dv/dt (Note 3), dv/dt .....                                    | 3.5V/ns                  |
| Operating Junction Temperature Range, $T_J$ .....                                  | -55° to +150° $^\circ C$ |
| Storage Temperature Range, $T_{stg}$ .....   | -55° to +150° $^\circ C$ |
| Lead Temperature (During Soldering, 1.6mm from case for 10sec), $T_L$ .....        | +300° $^\circ C$         |
| Mounting Torque (6-32 or M3 Screw) .....   | 10 lbf•in (1.1N•m)       |
| Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....                             | 0.83° $^\circ C/W$       |
| Thermal Resistance, Junction-to-Ambient, $R_{thJA}$ .....                          | 40° $^\circ C/W$         |
| Typical Thermal Resistance, Case-to-Sink (Flat, Greased Surface), $R_{thCS}$ ..... | 0.24° $^\circ C/W$       |

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 2.  $V_{DD} = 50V$ , starting  $T_J = +25^\circ C$ ,  $L = 11mH$ ,  $R_G = 25\pm$ ,  $I_{AS} = 8.8A$

Note 3.  $I_{SD} \leq 8.8A$ ,  $di/dt \leq 100A/\mu s$ ,  $V_{DD} \leq 500V$ ,  $T_J \leq +150^\circ C$

Note 4. Pules Width  $\leq$  300ms, Duty Cycle  $\leq$  2%.

**Electrical Characteristics:** ( $T_J = +25^\circ\text{C}$  unless otherwise specified)

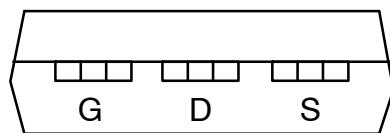
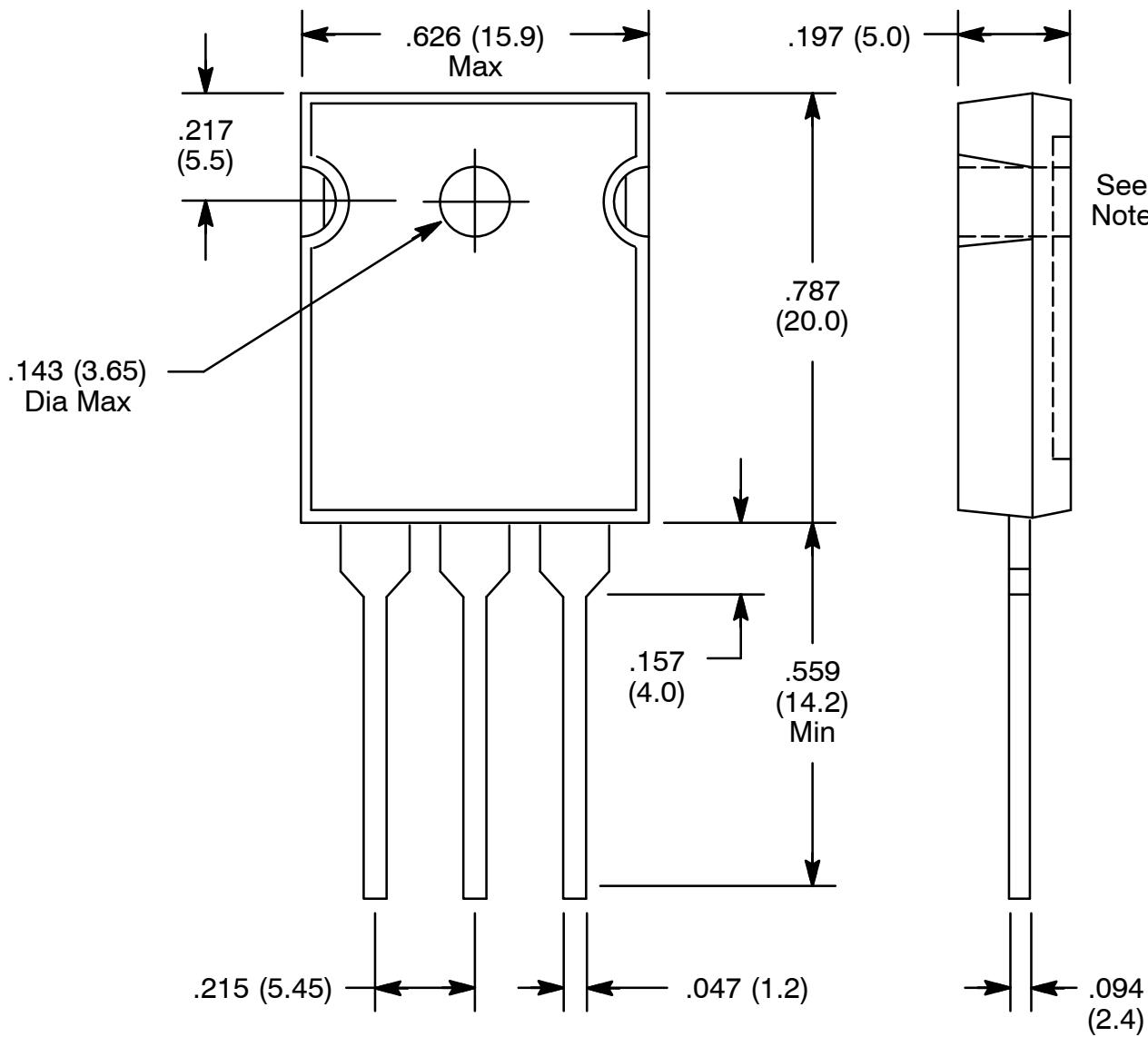
| Parameter                            | Symbol                                  | Test Conditions   | Min | Typ  | Max  | Unit                      |
|--------------------------------------|---|---|-----|------|------|---------------------------|
| Drain-to-Source Breakdown Voltage    | $V_{(\text{BR})\text{DSS}}$             | $V_{\text{GS}} = 0\text{V}, I_D = 250\text{mA}$                                       | 500 | -    | -    | V                         |
| Breakdown Voltage Temp. Coefficient  | $\frac{V_{(\text{BR})\text{DSS}}}{T_J}$ | Reference to $+25^\circ\text{C}$ , $I_D = 1\text{mA}$                                 | -   | 0.78 | -    | $\text{V}/^\circ\text{C}$ |
| Static Drain-to-Source On-Resistance | $R_{\text{DS}(\text{on})}$              | $V_{\text{GS}} = 10\text{V}, I_D = 5.3\text{A}$ , Note 4                              | -   | -    | 0.85 | $\pm$                     |
| Gate Threshold Voltage               | $V_{\text{GS}(\text{th})}$              | $V_{\text{DS}} = V_{\text{GS}}, I_D = 250\text{mA}$                                   | 2.0 | -    | 4.0  | V                         |
| Forward Transconductance             | $g_{\text{fs}}$                         | $V_{\text{DS}} = 50\text{V}, I_D = 5.3\text{A}$ , Note 4                              | 5.3 | -    | -    | mhos                      |
| Drain-to-Source Leakage Current      | $I_{\text{DSS}}$                        | $V_{\text{DS}} = 500\text{V}, V_{\text{GS}} = 0\text{V}$                              | -   | -    | 25   | $\text{mA}$               |
|                                      |   | $V_{\text{DS}} = 400\text{V}, V_{\text{GS}} = 0\text{V}, T_J = +125^\circ\text{C}$    | -   | -    | 250  | $\text{mA}$               |
| Gate-to-Source Forward Leakage       | $I_{\text{GSS}}$                        | $V_{\text{GS}} = 20\text{V}$  | -   | -    | 100  | nA                        |
| Gate-to-Source Reverse Leakage       | $I_{\text{GSS}}$                        | $V_{\text{GS}} = -20\text{V}$   | -   | -    | -100 | nA                        |
| Total Gate Charge                    | $Q_g$                                   | $I_D = 8\text{A}, V_{\text{DS}} = 400\text{V}, V_{\text{GS}} = 10\text{V}$ , Note 4   | -   | -    | 63   | nC                        |
| Gate-to-Source Charge                | $Q_{\text{gs}}$                         |   | -   | -    | 11   | nC                        |
| Gate-to-Drain ("Miller") Charge      | $Q_{\text{gd}}$                         |   | -   | -    | 30   | nC                        |
| Turn-On Delay Time                   | $t_{\text{d}(\text{on})}$               | $V_{\text{DD}} = 250\text{V}, I_D = 8\text{A}, R_G = 9.1\pm$ , $R_D = 31\pm$ , Note 4 | -   | 14   | -    | ns                        |
| Rise Time                            | $t_r$                                   |   | -   | 23   | -    | ns                        |
| Turn-Off Delay Time                  | $t_{\text{d}(\text{off})}$              |   | -   | 49   | -    | ns                        |
| Fall Time                            | $t_f$                                   |   | -   | 20   | -    | ns                        |
| Internal Drain Inductance            | $L_D$                                   | Between lead, .250in. (6.0) mm from package and center of die contact                 | -   | 5.0  | -    | nH                        |
| Internal Source Inductance           | $L_S$                                   |   | -   | 13   | -    | nH                        |
| Input Capacitance                    | $C_{\text{iss}}$                        | $V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1\text{MHz}$              | -   | 1300 | -    | pF                        |
| Output Capacitance                   | $C_{\text{oss}}$                        |   | -   | 310  | -    | pF                        |
| Reverse Transfer Capacitance         | $C_{\text{rss}}$                        |   | -   | 120  | -    | pF                        |

**Source-Drain Ratings and Characteristics:**

| Parameter                              | Symbol          | Test Conditions   | Min | Typ | Max | Unit          |
|--|-----------------|---|-----|-----|-----|---------------|
| Continuous Source Current (Body Diode) | $I_S$           |   | -   | -   | 8.8 | A             |
| Pulsed Source Current (Body Diode)     | $I_{\text{SM}}$ | Note 1  | -   | -   | 35  | A             |
| Diode Forward Voltage                  | $V_{\text{SD}}$ | $T_J = +25^\circ\text{C}, I_S = 8.8\text{A}, V_{\text{GS}} = 0\text{V}$ , Note 4        | -   | -   | 2.0 | V             |
| Reverse Recovery Time                  | $t_{\text{rr}}$ | $T_J = +25^\circ\text{C}, I_F = 8\text{A}$ , $dI/dt = 100\text{A}/\mu\text{s}$ , Note 4 | -   | 460 | 970 | ns            |
| Reverse Recovery Charge                | $Q_{\text{rr}}$ |   | -   | 3.5 | 7.6 | $\mu\text{C}$ |
| Forward Turn-On Time                   | $t_{\text{on}}$ | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )               |     |     |     |               |

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 4. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .



TO247

**Note:** Drain connected to metal part of mounting surface.